

ABSTRACT

To provide an Al bonding wire for semiconductor devices that stably exhibits a favorable bonding strength
5 at a second bonded part. An Al bonding wire for semiconductor devices containing equal to or larger than 0.01 mass% and smaller than 0.8 mass% of one or more of Sc, Zr, and Mg in total, wherein, as a result of measuring a crystal orientation on a cross-section parallel to a wire
10 axis direction including a wire axis of the bonding wire, an orientation ratio of a <100> crystal orientation angled at 15 degrees or less to the wire axis direction is equal to or higher than 30% and equal to or lower than 90%.

15 FIG. 1